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APPLICATION NO.	FILING DATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/894,460	06/28/2001	Kevin G. Donohoe	400.100US01	6410

27073 7590 03/27/2003

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EXAMINER

ANYA, IGWE U

ART UNIT	PAPER NUMBER
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2825

DATE MAILED: 03/27/2003

Please find below and/or attached an Office communication concerning this application or proceeding.

# Office Action Summary

Application No.

09/894,460

Applicant(s)

DONOHOE, KEVIN G.

Examiner

Igwe U. Anya

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-- The MAILING DATE of this communication appears on the cover sheet with the correspondence address --

## Period for Reply

A SHORTENED STATUTORY PERIOD FOR REPLY IS SET TO EXPIRE 3 MONTH(S) FROM THE MAILING DATE OF THIS COMMUNICATION.

- Extensions of time may be available under the provisions of 37 CFR 1.136(a). In no event, however, may a reply be timely filed after SIX (6) MONTHS from the mailing date of this communication.
- If the period for reply specified above is less than thirty (30) days, a reply within the statutory minimum of thirty (30) days will be considered timely.
- If NO period for reply is specified above, the maximum statutory period will apply and will expire SIX (6) MONTHS from the mailing date of this communication.
- Failure to reply within the set or extended period for reply will, by statute, cause the application to become ABANDONED (35 U.S.C. § 133).
- Any reply received by the Office later than three months after the mailing date of this communication, even if timely filed, may reduce any earned patent term adjustment. See 37 CFR 1.704(b).

## Status

- 1) ☒ Responsive to communication(s) filed on 28 June 2001.
- 2a) ☐ This action is **FINAL**. 2b) ☒ This action is non-final.
- 3) ☐ Since this application is in condition for allowance except for formal matters, prosecution as to the merits is closed in accordance with the practice under *Ex parte Quayle*, 1935 C.D. 11, 453 O.G. 213.

## Disposition of Claims

- 4) ☒ Claim(s) 1-56 is/are pending in the application.
- 4a) Of the above claim(s) \_\_\_\_\_ is/are withdrawn from consideration.
- 5) ☐ Claim(s) \_\_\_\_\_ is/are allowed.
- 6) ☒ Claim(s) 1-56 is/are rejected.
- 7) ☐ Claim(s) \_\_\_\_\_ is/are objected to.
- 8) ☐ Claim(s) \_\_\_\_\_ are subject to restriction and/or election requirement.

## Application Papers

- 9) ☐ The specification is objected to by the Examiner.
- 10) ☒ The drawing(s) filed on 28 June 2001 is/are: a) ☒ accepted or b) ☐ objected to by the Examiner.
- Applicant may not request that any objection to the drawing(s) be held in abeyance. See 37 CFR 1.85(a).
- 11) ☐ The proposed drawing correction filed on \_\_\_\_\_ is: a) ☐ approved b) ☐ disapproved by the Examiner.
- If approved, corrected drawings are required in reply to this Office action.
- 12) ☐ The oath or declaration is objected to by the Examiner.

## Priority under 35 U.S.C. §§ 119 and 120

- 13) ☐ Acknowledgment is made of a claim for foreign priority under 35 U.S.C. § 119(a)-(d) or (f).
- a) ☐ All b) ☐ Some \* c) ☐ None of:
1. ☐ Certified copies of the priority documents have been received.
2. ☐ Certified copies of the priority documents have been received in Application No. \_\_\_\_\_.
3. ☐ Copies of the certified copies of the priority documents have been received in this National Stage application from the International Bureau (PCT Rule 17.2(a)).
- \* See the attached detailed Office action for a list of the certified copies not received.
- 14) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. § 119(e) (to a provisional application).
- a) ☐ The translation of the foreign language provisional application has been received.
- 15) ☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.

## Attachment(s)

- 1) ☒ Notice of References Cited (PTO-892)
- 2) ☐ Notice of Draftsperson's Patent Drawing Review (PTO-948)
- 3) ☒ Information Disclosure Statement(s) (PTO-1449) Paper No(s) 3.
- 4) ☐ Interview Summary (PTO-413) Paper No(s). \_\_\_\_\_
- 5) ☐ Notice of Informal Patent Application (PTO-152)
- 6) ☐ Other: \_\_\_\_\_

**DETAILED ACTION**

***Claim Rejections - 35 USC § 103***

1. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:

(a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negated by the manner in which the invention was made.

2. Claims 5, 8, 12, 19 – 40, 42, 50, 52 – 56 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mui et al. (US Patent 6235643) in view of Hause et al. (US Patent 6051863).

3. Mui et al. teach forming an aperture in a silicon oxide layer, comprising:  
plasma-etching with fluorine containing gas in addition to a selection from bromine containing gas and or iodine containing gas (col. 17 lines 1 – 8), thereby depositing a passivating polymer residue (508) on the sidewalls of the aperture, the aperture is tapered (col. 1 lines 60 – 67) with a slope angle greater than 87 degrees (figs 6), bromine gas selected from hydrogen bromide, bromine-substituted fluorocarbon, bromotrifluoromethane and bromine-substituted hydrofluorocarbon and the fluorine source selected from a group of perfluorocarbons and hydrofluorocarbons and the additional gas added prior to forming the polymer residue (col. 3 lines 4 – 28). Further taught is the use of HBr as profile control additive (col. 8 lines 8 – 17).
4. Hause et al. teach the adsorption of bromine atoms in a silicon oxide dielectric during plasma etching (col. 7 lines 34 – 37).

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5. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the teachings of Hause et al. into the Mui et al. reference to perform an anisotropic etch with low energy ions. Adsorption of low energy ions by matter (silicon oxide) is chemistry inherent.

6. Claims 5, 8, 12, 19 – 40, 42, 50, 52 – 56 are rejected under 35 U.S.C. 103(a) as being unpatentable over Mui et al. (US Patent 6235643) in view of Hause et al. (US Patent 6051863), and further in view of Wong et al. (US Patent 5874362).

7. The Mui/Hause et al. reference teaches the features previously outlined but lacks the step of etching with an iodinate etching gas selected from hydrogen iodide, iodine-substituted fluorocarbon, iodotrifluoromethane and iodine-substituted hydrofluorocarbon, the aperture aspect ratio is greater than 5:1, and 8:1, wherein the bottom width is greater than 60% of the top width at desired aspect ratio, the additional gas added after forming the polymer residue, and a bias power of at least 900 watts.

8. However, Wong et al. teach etching with an iodinate etching gas selected from hydrogen iodide, iodine-substituted fluorocarbon, iodotrifluoromethane and iodine-substituted hydrofluorocarbon, the aperture aspect ratio is greater than 5:1, and 8:1 (col. 5 lines 45 – 51).

9. Therefore, it would have been obvious to one of ordinary skill in the art at the time the invention was made to incorporate the teachings of Wong et al. into the Mui/Hause et al. reference to form apertures in silicon oxide with high aspect ratios. Furthermore, where the general conditions are disclosed in prior art, provision of

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adjustability where needed, involves only routine skill in the art. In re Stevens, 101 USPQ 284 (CCPA).

10. Prior art considered but not used in the rejections include Zhou et al. (US Patent 6017826), Trapp et al. (US Patent 6451705), and Wang et al. (US Patent 6127278).

11. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Igwe U. Anya whose telephone number is (703) 308-3549. The examiner can normally be reached on M - F 8:30am - 5:00pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Matthew S. Smith can be reached on (703) 308-1323. The fax phone numbers for the organization where this application or proceeding is assigned are (703) 872-9318 for regular communications and (703) 872-9319 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding should be directed to the receptionist whose telephone number is (703) 308-0956.

Igwe U. Anya  
Examiner  
Art Unit 2825

IA  
March 20, 2003



MATTHEW SMITH  
SENIOR PATENT EXAMINER  
TECHNOLOGY CENTER 2800